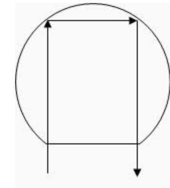
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Notch or Flat	Notch	Wafer Vendor
	4.0	Secondary Flat Orientation	None	Wafer Vendor
	5.0	Overall Thickness	700.00 +/- 26.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 100%
	8.0	Warp	<80.00µm	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	675.00 +/- 25.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.001 ~ 0.005 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Lapped and etched with poly oxide seal and Lasermark.	Wafer Vendor
BuriedOxide	18.0	Oxide Type	None	
DeviceSilicon	19.0	Device Growth Method	FZ	Wafer Vendor
	20.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	21.0	Nominal Thickness	25.00 +/- 1.00 µm	Filmetrics 9 Point, 100%
	22.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	23.0	Edge Removal Depth in Handle	<100um	Guaranteed by process
	24.0	Device Doping Type	P	Wafer Vendor
	25.0	Device Dopant	Boron	Wafer Vendor
	26.0	Device Resistivity	>1000 Ohmcm	Wafer Vendor
	27.0	Voids	none	Bright Light, 100% (note 2)
	28.0	Scratches	<25mm Total Length	Bright Light, 100% (note 2)
	29.0	Haze	none	Bright Light, 100% (note 2)

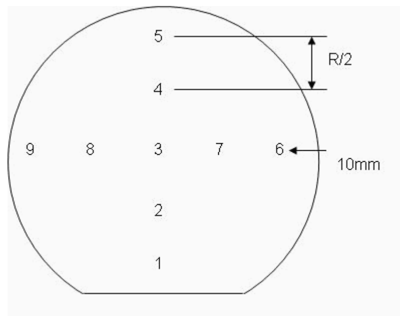
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information